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# The use of magnetic fields in industrial growth of single silicon crystals

June 13, 2002 / Janis Virbulis

PERFECT SILICON SOLUTIONS

# Outline

- Melt convection
- Why magnetic fields are used?
- Types of magnetic fields
- Wacker network of collaborations





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## **Melt convection**

Melt convection in large CZ crucible is turbulent (Gr about 10<sup>10</sup> in 32" crucible)

- time dependent
- non-symmetric
- large fluctuations of velocity and temperature



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#### **Melt convection**



# Melt convection...

## ... can be influenced by:

- Rotation of crucible
- Rotation of crystal
- Argon gas flow rate
- Argon pressure
- Hot zone (heat shield) design

## It's all !

 Heater Power is adjusted in manner to keep the required pulling velocity and crystal diameter

# + magnetic field(s)

# Why magnetic fields are used?

- to increase the **yield**
- to fulfill the quality requirements

**GfS Yield** - Good for Structure (dislocation free part)

Reason of dislocations: stress limit exceeded at interface Reason: - particle incorporated in crystal

- temperature fluctuation

(larger crucibles - larger fluctuations)

**GfO Yield** - Good for Order (part which corresponds to customer requirements)

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# Why magnetic fields are used?

#### **Quality measures**

Dopant distribution

- concentration (increases during the growth of crystal)
- radial variation (thickness of concentration boundary layer on interface)
- striations (temperature and flow fluctuations at the growth interface)

#### Oxygen distribution

- concentration (very complex behavior)
- radial distribution (flow near the crystal no boundary layer on the interface!)
- striations (flow fluctuations in the bulk)

Distribution of point defect agglomerates

- type of defects (depends on temperature gradient on the interface)
- size and density (no direct dependence on melt flow)

Steady magnetic fields

j~v×B





Transversal



Early 70's

Early 80's

End of 80's

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Advantages of steady magnetic fields

- •Reduction of temperature fluctuations
- Influence of oxygen concentration (lower oxygen)

#### **Disadvantages of steady magnetic fields**

- Higher crucible temperature (corrosion)
- Lorenz force coupled to velocity, instabilities can appear
- Axial field: insufficient radial dopant and oxygen homogeneity
- Transversal field : striations due to non-symmetric flow and temperature field



#### **Time-dependent magnetic fields**

**j ~** ω**B** 

**Rotating field** 



Influence like to time-dependent field

**EMCZ** 



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Combined field

**Travelling field** 





The use of magnetic fields in industrial

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growth of single silicon crystals

#### **Effect of magnetic fields**



### **Effect of magnetic fields**



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Advantages of time-dependent magnetic fields

- •Flow is influenced actively, totally different flow patterns possible
- Influence of oxygen concentration (higher oxygen)
- Lower crucible temperature
- At least 10 x lower field intensity as for steady fields
- Lorenz force independent on flow velocity

**Disadvantages of time dependent magnetic fields** 

• Higher flow velocities (but more stable than buoyancy)



# Wacker network of collaborations

#### Melt flow related collaborations



## Summary

• Magnetic fields are good instrument for yield and quality improvement for 300 mm crystal growth

Alternating, combined and travelling magnetic fields are used for 300 mm crystal growth

• Successful implementation of new magnetic fields was possible only in team with our collaborations



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